FUJI ELECTRIC

6MBI 10GS-060

6-Pack IGBT
600 V
10 A

IGBT MODULE (Single-in-Line)

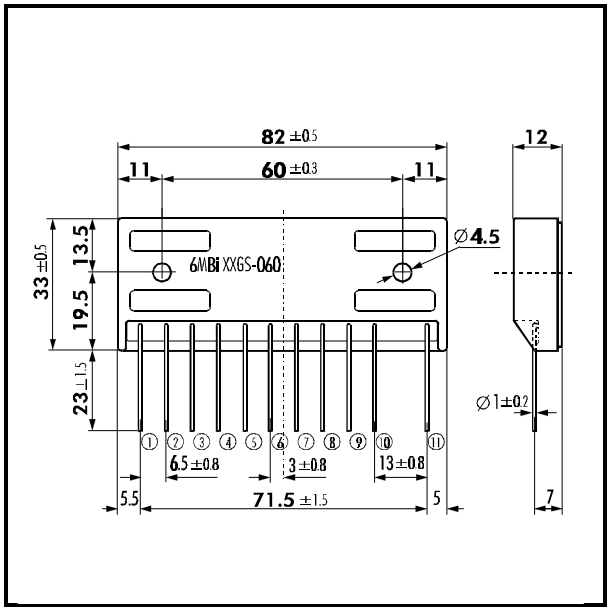
■ Features

- *Square RBSOA*
- *Low Saturation Voltage*
- *Improved FWD Characteristic*
- *Minimized Internal Stray Inductance*

■ Applications

- *High Power Switching*
- *A.C. Motor Controls*
- *D.C. Motor Controls*

■ Outline Drawing



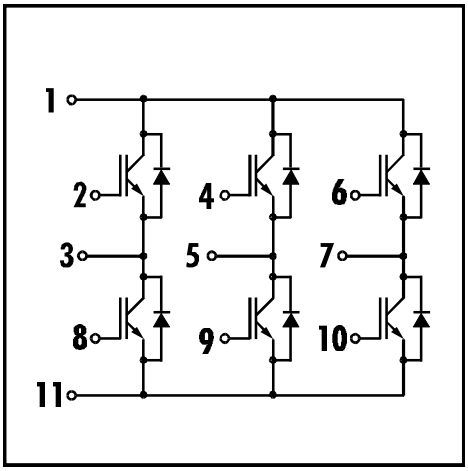
■ Maximum Ratings and Characteristics

• Absolute Maximum Ratings (T_c=25°C)

Items		Symbols	Ratings	Units
Collector-Emitter Voltage		V_{CES}	600	V
Gate -Emitter Voltage		V_{GES}	± 20	V
Collector Current	Continuous	I_C	10	A
	1ms	$I_{C\ PULSE}$	20	
	Continuous	$-I_C$	10	
	1ms	$-I_{C\ PULSE}$	20	
Max. Power Dissipation		P_C	45	W
Operating Temperature		T_j	+150	°C
Storage Temperature		T_{stg}	-40 ~ +125	°C
Isolation Voltage	A.C. 1min.	V_{is}	2000	V
Screw Torque		Mounting *1	1.7	Nm

Note: *1:Recommendable Value; 1.3 ~ 1.7 Nm (M4)

■ Equivalent Circuit



• Electrical Characteristics (at T_j=25°C)

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I_{CES}	V_{GE}=0V V_{CE}=600V			1.0	mA
Gate-Emitter Leackage Current	I_{GES}	V_{CE}=0V V_{GE}=± 20V			100	nA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	V_{GE}=20V I_C=10mA	5.5		8.5	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V_{GE}=15V I_C=10A			2.8	V
Input capacitance	C_{ies}	V_{GE}=0V		650		pF
Output capacitance	C_{oes}	V_{CE}=10V		150		
Reverse Transfer capacitance	C_{res}	f=1MHz		36		
Turn-on Time	t_{ON}	V_{CC}=300V			1.2	µs
	t_r	I_C=10A			1.0	
Turn-off Time	t_{OFF}	V_{GE}=± 15V			1.0	
	t_f	R_G=220Ω			0.35	
Diode Forward On-Voltage	V_F	I_F=10A V_{GE}=0V			3.0	V
Reverse Recovery Time	t_{rr}	I_F=10A			300	ns

• Thermal Characteristics

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	$R_{th(j-c)}$	IGBT			2.78	°C/W
	$R_{th(j-c)}$	Diode			4.50	
	$R_{th(c-f)}$	With Thermal Compound		0.06		

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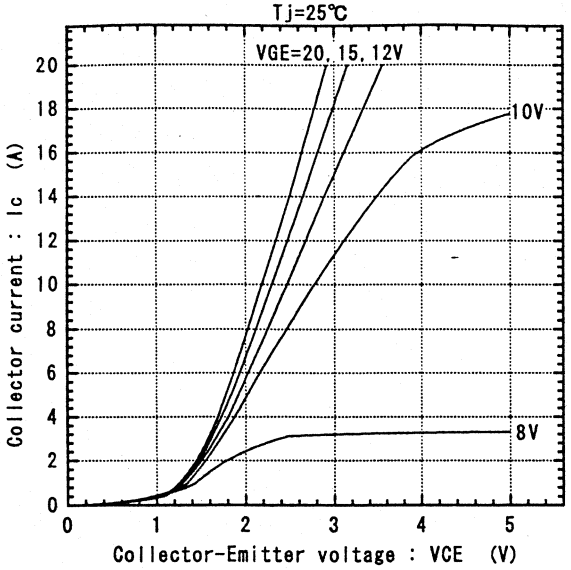
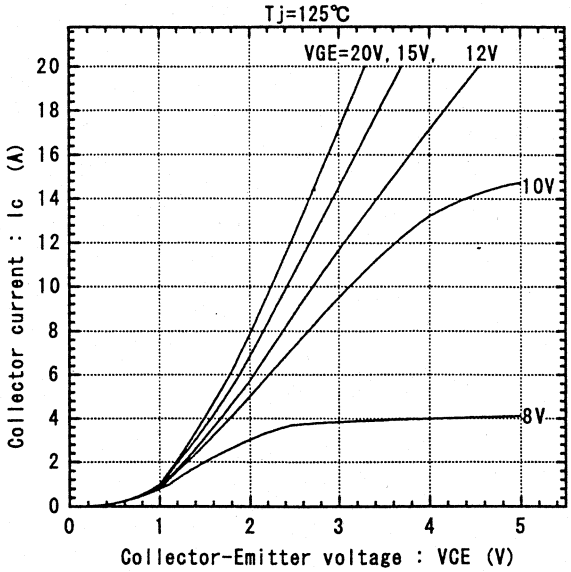
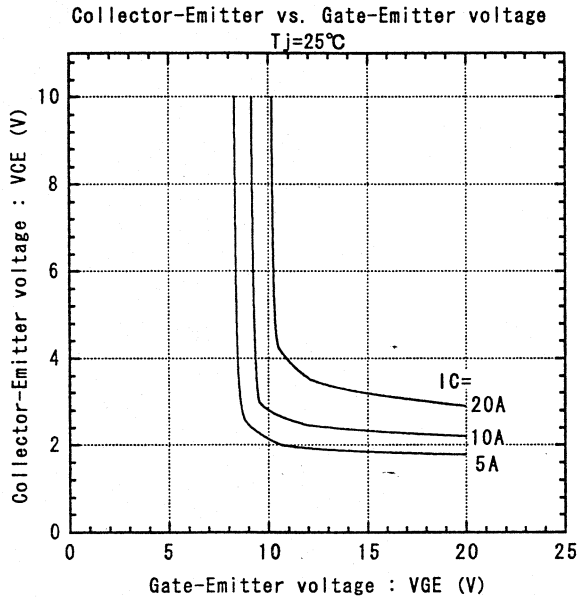
Collector-Emitter voltage vs. Collector current
Tj=25℃



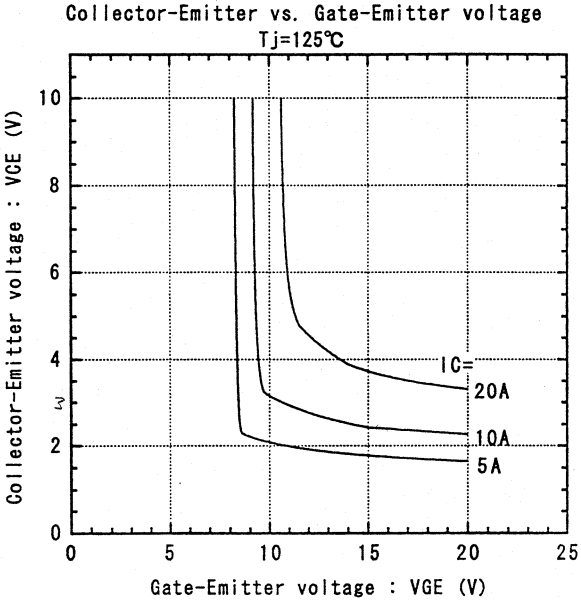
Collector-Emitter voltage vs. Collector current
Tj=125℃



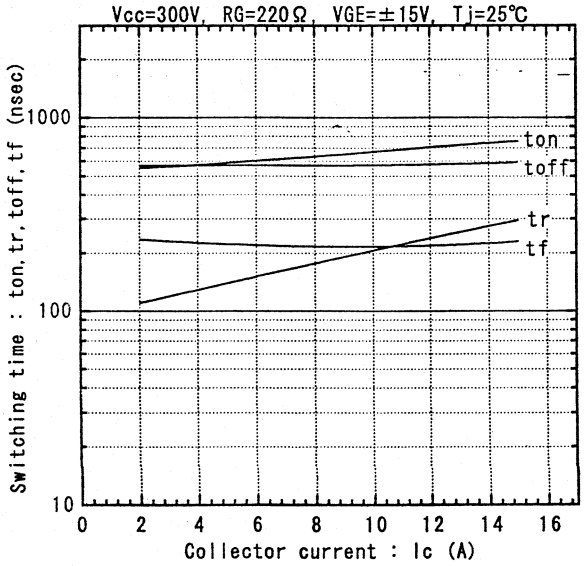
Collector-Emitter vs. Gate-Emitter voltage
Tj=25℃



Collector-Emitter vs. Gate-Emitter voltage
Tj=125℃



Switching time vs. Collector current
Vcc=300V, RG=220Ω, VGE=±15V, Tj=25℃



Switching time vs. Collector current
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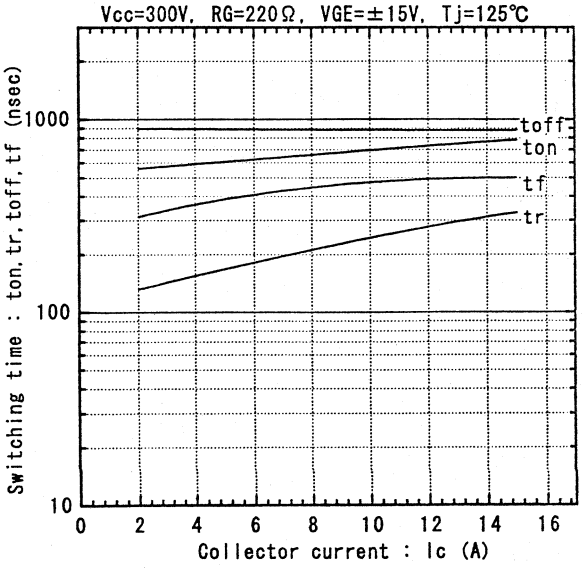

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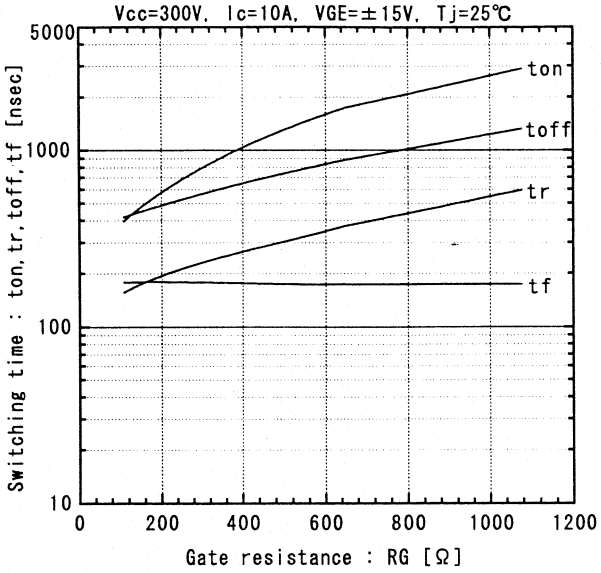
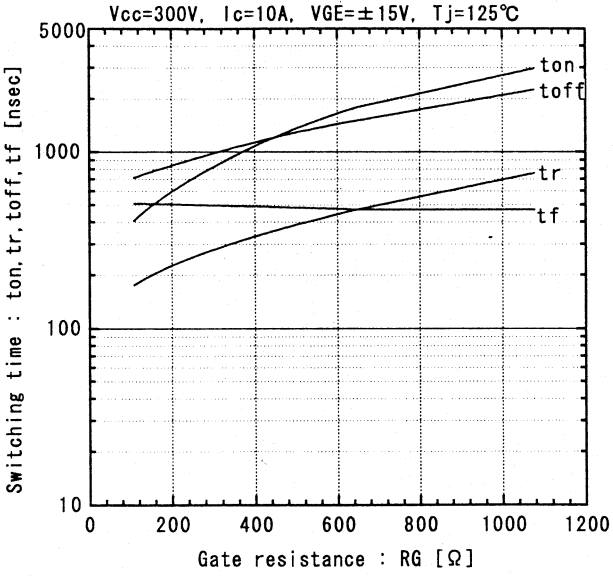
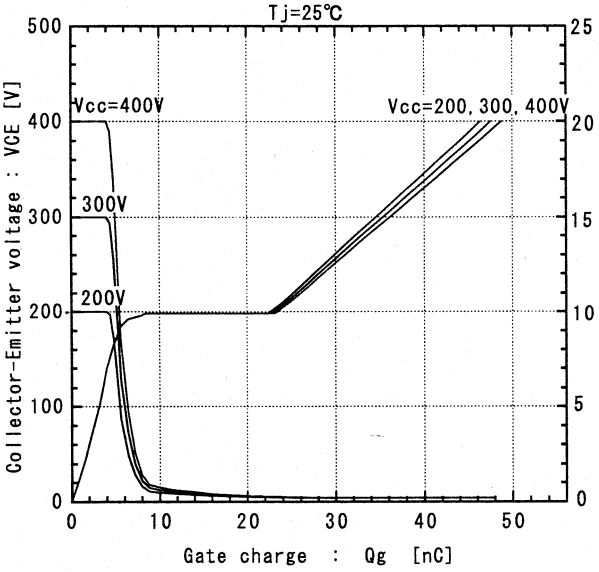
Switching time vs. Gate resistance
Vcc=300V, Ic=10A, VGE=±15V, Tj=25℃



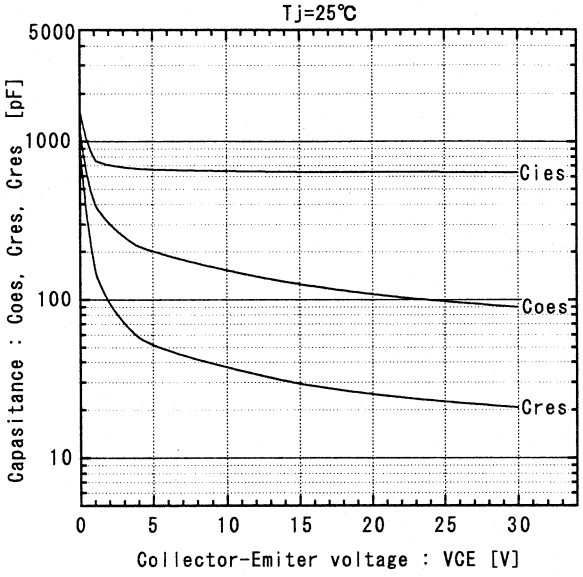
Switching time vs. Gate resistance
Vcc=300V, Ic=10A, VGE=±15V, Tj=125℃



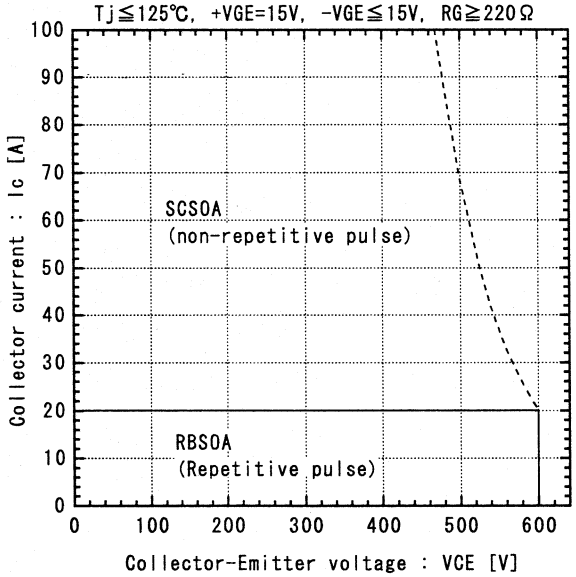
Dynamic input charactristics
Tj=25℃



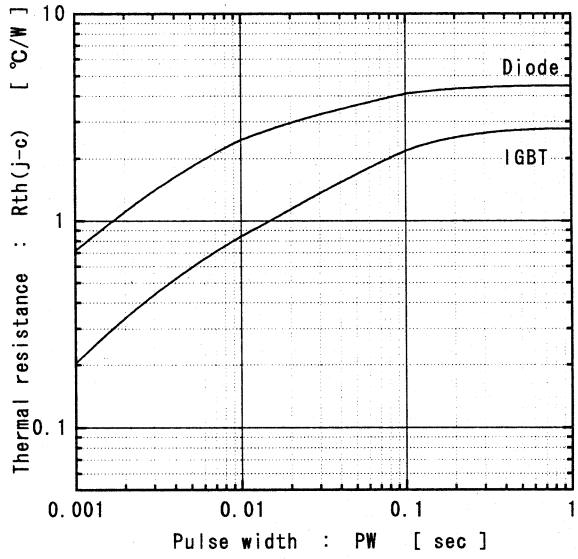
Capacitance vs. Collector-Emitter voltage
Tj=25℃

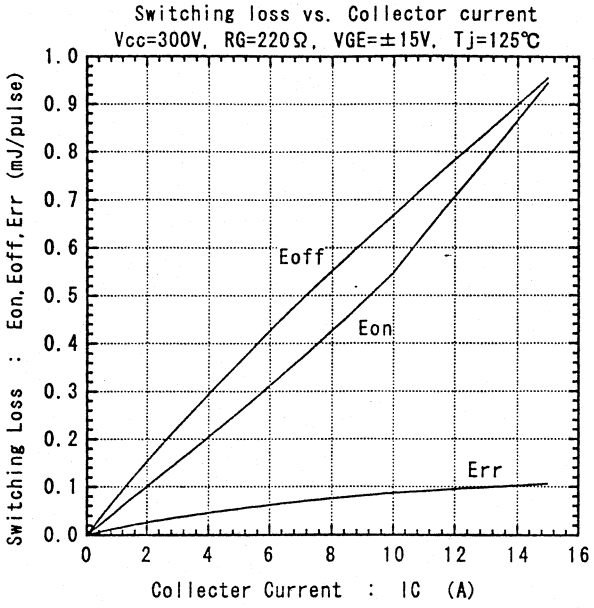


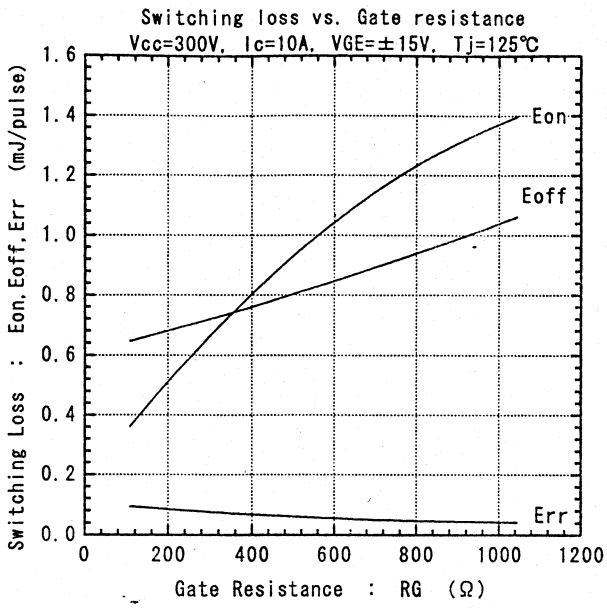
Reverse biased safe orerating area
Tj≦125℃, +VGE=15V, -VGE≦15V, RG≧220Ω

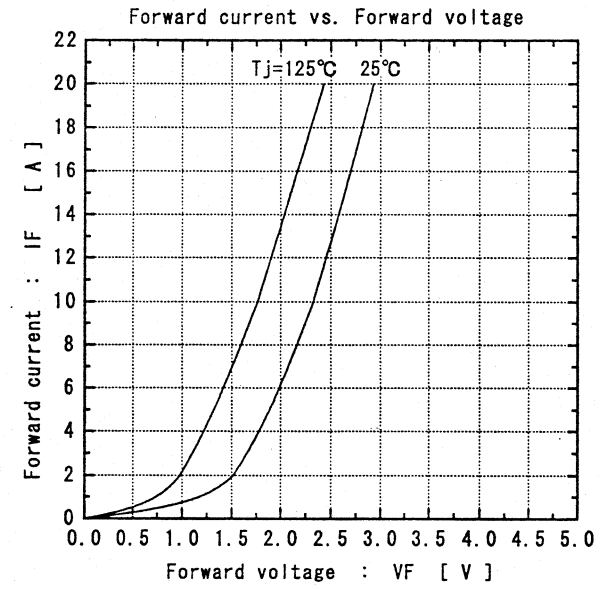


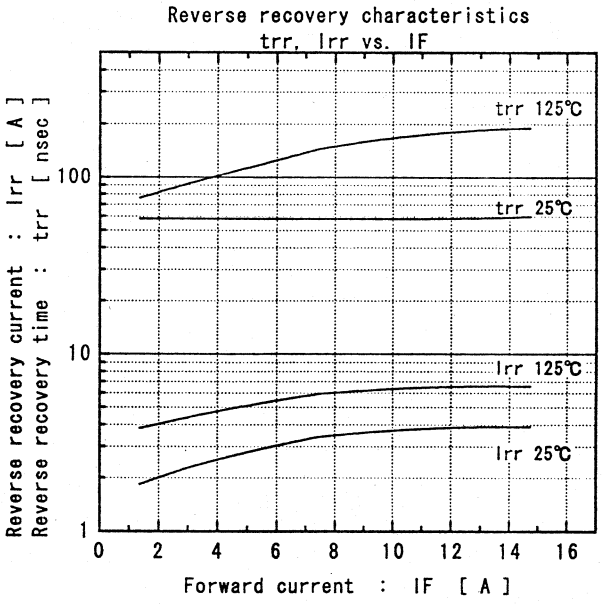
Transient thermal resistance











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